NSN 5962-01-366-3039

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View Online at https://aerobasegroup.com/nsn/5962-01-366-3039

Body Length:
1.490 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.217 inches
Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Monolithic and parallel operation
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Input Circuit Pattern:
12 input
Case Outline Source And Designator:
D-10 mil-m-38510
Current Rating Per Characteristic:
50.00 milliamperes average forward current averaged over a full 60-hz cycle not applicable
Terminal Surface Treatment:
Solder
Product Name:
Parallel fifo
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Capitance Rating Per Characteristic:
8.00 input picofarads and 8.00 output picofarads
Time Rating Per Chacteristic:
30.00 nanoseconds af output megawatts
Memory Device Type:
First-in first-out
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:

28 printed circuit

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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